

# HL6557MG

## AlGaInP Laser Diodes

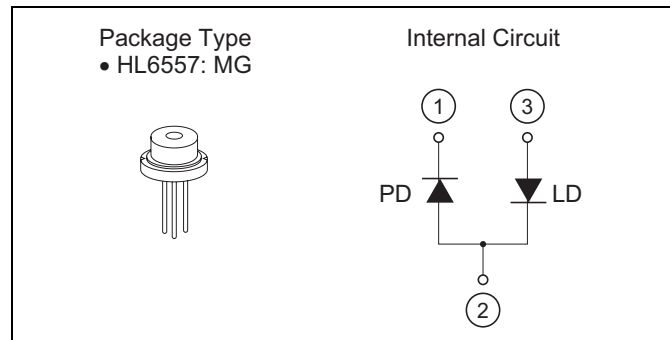
ODE-208-053 (Z)  
Preliminary  
Rev.0  
Feb. 22, 2007

### Description

The HL6557MG is a 0.65  $\mu\text{m}$  band AlGaInP laser diode (LD) with a multi-quantum well (MQW) structure. It is suitable as light sources in bar code readers, laser levelers and various other types of optical equipment.

### Features

- Visible light output :  $\lambda_p = 658 \text{ nm}$  Typ
- Single longitudinal mode
- Optical output power : 10 mW CW
- Low operating voltage : 2.8 V Max
- Built-in photodiode for monitoring laser output
- Small package :  $\phi 5.6 \text{ mm}$



### Absolute Maximum Ratings

( $T_C = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Optical output power	$P_O$	12	mW
LD reverse voltage	$V_{R(LD)}$	2	V
PD reverse voltage	$V_{R(PD)}$	30	V
Operating temperature	$T_{opr}$	-10 to +70	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to +85	$^\circ\text{C}$

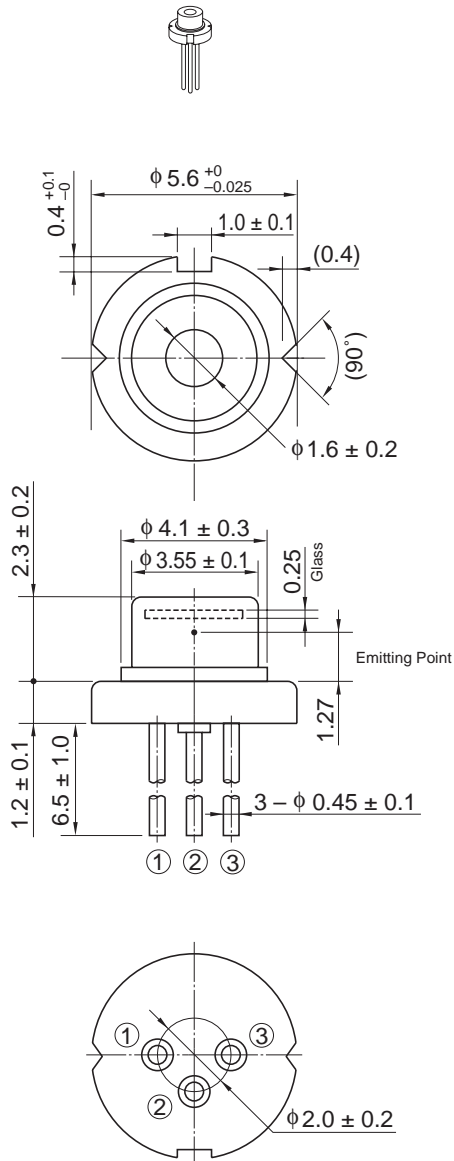
### Optical and Electrical Characteristics

( $T_C = 25^\circ\text{C}$ )

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Threshold current	$I_{th}$	30	45	70	mA	—
Operating current	$I_{OP}$	—	60	90	mA	$P_O = 10 \text{ mW}$
Operating voltage	$V_{OP}$	—	—	2.8	V	$P_O = 10 \text{ mW}$
Beam divergence parallel to the junction	$\theta_{//}$	7	8.5	10.5	$^\circ$	$P_O = 10 \text{ mW}$
Beam divergence perpendicular to the junction	$\theta_{\perp}$	18	22	26	$^\circ$	$P_O = 10 \text{ mW}$
Astigmatism	$A_s$	—	6	—	—	$P_O = 5 \text{ mW}$ , $NA = 0.55$
Lasing wavelength	$\lambda_p$	645	658	665	nm	$P_O = 10 \text{ mW}$
Monitor current	$I_s$	0.03	0.07	0.15	mA	$P_O = 10 \text{ mW}$ , $V_{R(PD)} = 5 \text{ V}$

Package Dimensions

As of July, 2002  
Unit: mm



OPJ Code	LD/MG
JEDEC	—
JEITA	—
Mass (reference value)	0.3 g

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1. The laser light is harmful to human body especially to eye no matter what directly or indirectly. The laser beam shall be observed or adjusted through infrared camera or equivalent.
2. This product contains gallium arsenide (GaAs), which may seriously endanger your health even at very low doses. Please avoid treatment which may create GaAs powder or gas, such as disassembly or performing chemical experiments, when you handle the product.  
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3. Definition of items shown in this CAS is in accordance with that shown in Opto Device Databook issued by OPJ unless otherwise specified.

## Sales Offices



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